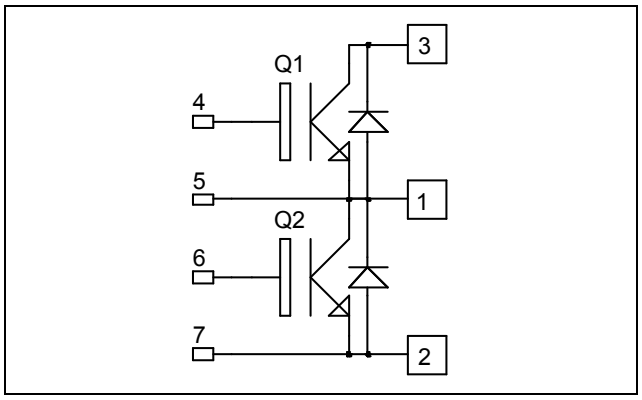
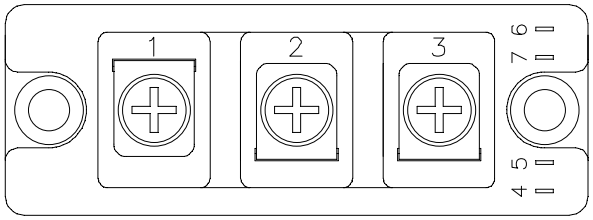
Phase leg NPT IGBT Power Module

V_{CES} = 600V
I_C = 165A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M5 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	230	A
		T_C = 80°C	165	
I_{CM}	Pulsed Collector Current	T_C = 25°C	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	781	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	400A@420V	

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 600V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V I_C = 200A	T_j = 25°C		1.95	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, I_C = 4 mA		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz			9000		pF
C_{res}	Reverse Transfer Capacitance				800		
Q_G	Gate charge	V_{GE}=15V, I_C=200A V_{CE}=300V			650		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 200A R_G = 16Ω			150		ns
T_r	Rise Time				72		
$T_{d(off)}$	Turn-off Delay Time				530		
T_f	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 200A R_G = 16Ω			160		ns
T_r	Rise Time				75		
$T_{d(off)}$	Turn-off Delay Time				550		
T_f	Fall Time				50		
E_{on}	Turn on energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 200A R_G = 16Ω	T_j = 125°C		9		mJ
E_{off}	Turn off energy		T_j = 125°C		8.5		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p ≤ 10µs ; T_j = 125°C			900		A

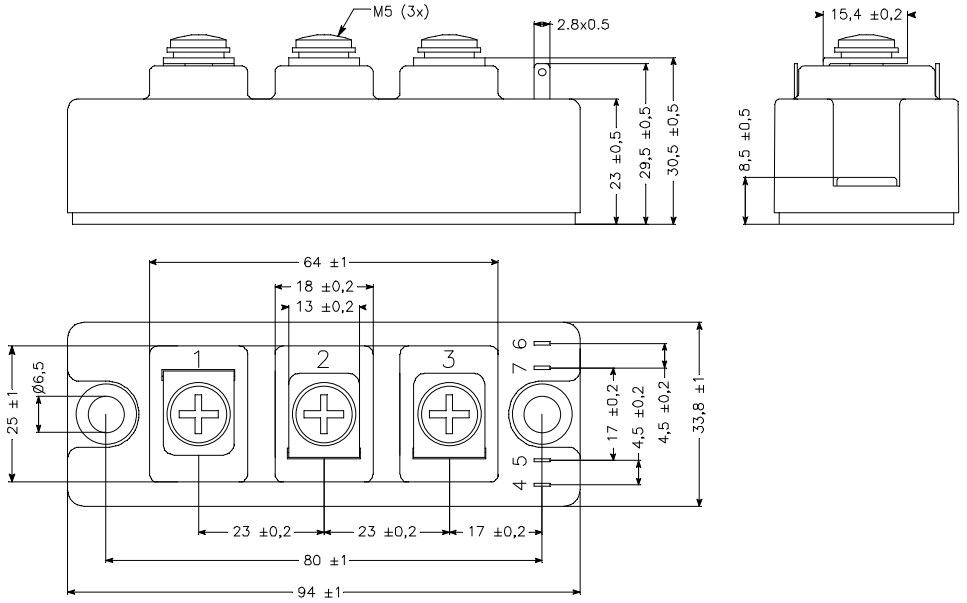
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			100	µA
			T_j = 125°C			500	
I_F	DC Forward Current		Tc = 80°C		200		A
V_F	Diode Forward Voltage	I_F = 200A V_{GE} = 0V	T_j = 25°C		1.25	1.6	V
			T_j = 125°C		1.2		
t_{rr}	Reverse Recovery time	I_F = 200A V_R = 300V di/dt =3500A/µs	T_j = 25°C		150		ns
			T_j = 125°C		250		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		13		µC
			T_j = 125°C		20		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		2.9		mJ
			T_j = 125°C		5.7		

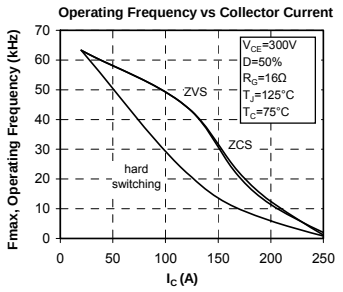
Thermal and package characteristics

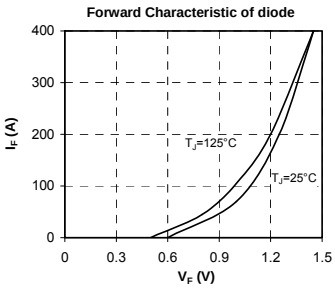
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.16	°C/W
			Diode			0.30	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M5	2		3.5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					180	g

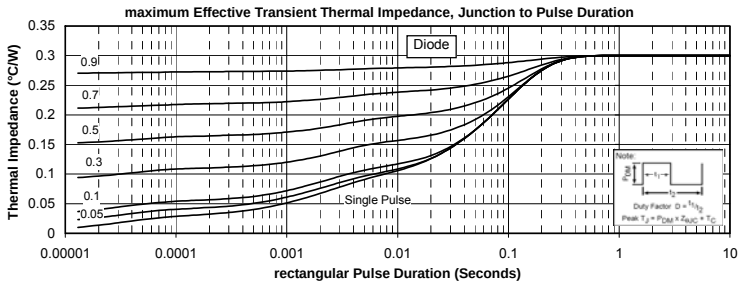
D1 Package outline (dimensions in mm)



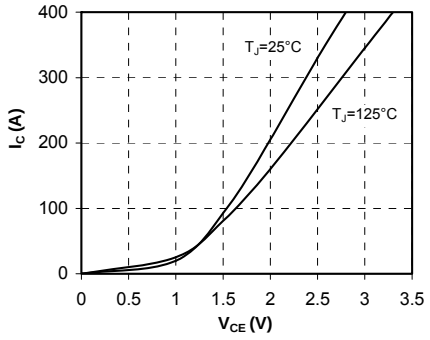
Typical Performance Curve



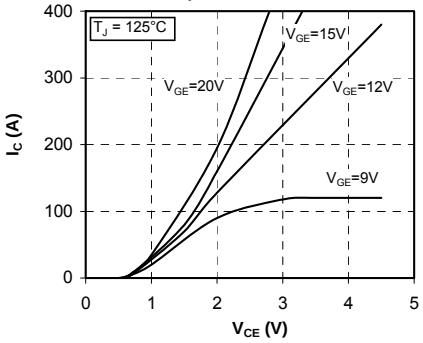




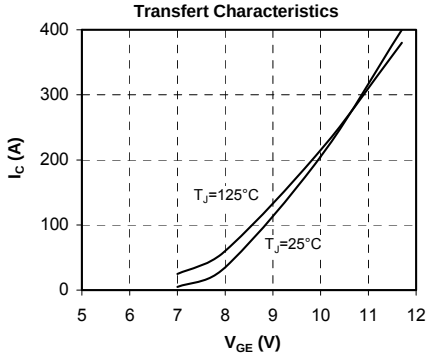
Output Characteristics (V_{GE}=15V)



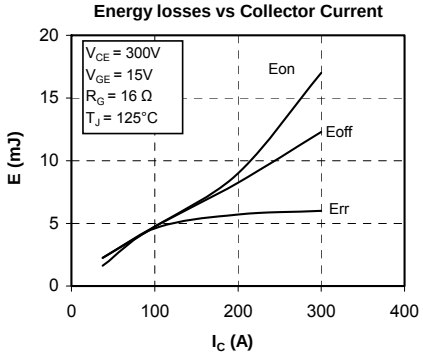
Output Characteristics



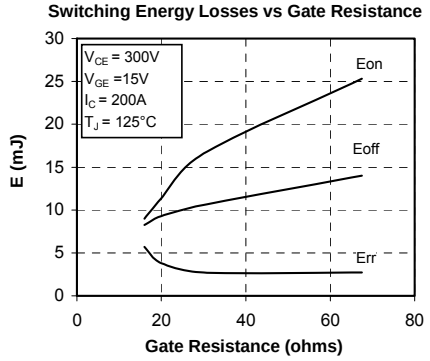
Transfert Characteristics



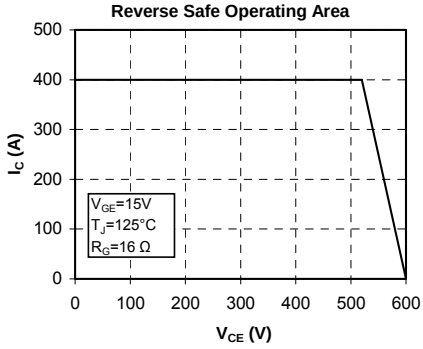
Energy losses vs Collector Current



Switching Energy Losses vs Gate Resistance



Reverse Safe Operating Area



maximum Effective Transient Thermal Impedance, Junction to Pulse Duration